

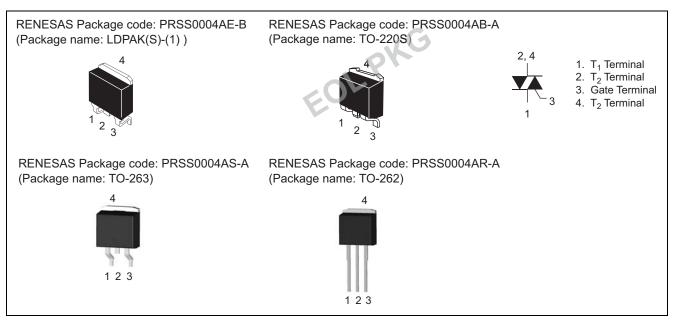
# BCR10CS-12LB

## 600V-10A-Triac Medium Power Use

Features

- I<sub>T (RMS)</sub> : 10 A
- V<sub>DRM</sub> : 600 V
- $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGT III}$ : 30 mA (20 mA)<sup>Note6</sup>
- The product guaranteed maximum junction temperature of 150°C
- Non-Insulated Type
- Planar Passivation Type

## Outline



### Applications

Contactless AC switch, light dimmer, electronic flasher unit, control of household equipment such as TV sets, stereo systems, refrigerator, washing machine, infrared kotatsu, carpet, electric fan, solenoid driver, small motor control, solid state relay, copying machine, electric tool, electric heater control, and other general purpose control applications

#### **Maximum Ratings**

| Parameter                                              | Symbol           | Voltage class | Unit |
|--------------------------------------------------------|------------------|---------------|------|
| Repetitive peak off-state voltage <sup>Note1</sup>     | Vdrm             | 600           | V    |
| Non-repetitive peak off-state voltage <sup>Note1</sup> | V <sub>DSM</sub> | 720           | V    |

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#### BCR10CS-12LB

| Parameter                      | Symbol               | Ratings      | Unit             | Conditions                                                                                 |
|--------------------------------|----------------------|--------------|------------------|--------------------------------------------------------------------------------------------|
| RMS on-state current           | I <sub>T (RMS)</sub> | 10           | A                | Commercial frequency, sine full wave $360^{\circ}$ conduction, Tc = $128^{\circ}C^{Note3}$ |
| Surge on-state current         | Ітѕм                 | 100          | A                | 60Hz sinewave 1 full cycle, peak value, non-repetitive                                     |
| I <sup>2</sup> t for fusing    | l <sup>2</sup> t     | 41.6         | A <sup>2</sup> s | Value corresponding to 1 cycle of half<br>wave 60Hz, surge on-state current                |
| Peak gate power dissipation    | P <sub>GM</sub>      | 5            | W                |                                                                                            |
| Average gate power dissipation | P <sub>G (AV)</sub>  | 0.5          | W                |                                                                                            |
| Peak gate voltage              | $V_{GM}$             | 10           | V                |                                                                                            |
| Peak gate current              | I <sub>GM</sub>      | 2            | А                |                                                                                            |
| Junction temperature           | Tj                   | - 40 to +150 | °C               |                                                                                            |
| Storage temperature            | Tstg                 | - 40 to +150 | °C               |                                                                                            |
| Mass                           | _                    | 1.3          | g                | Typical value                                                                              |

Notes: 1. Gate open.

#### **Electrical Characteristics**

| Parameter                                                              |      | Symbol              | Min.    | Тур. | Max.                | Unit | Test conditions                                                                                                       |
|------------------------------------------------------------------------|------|---------------------|---------|------|---------------------|------|-----------------------------------------------------------------------------------------------------------------------|
| Repetitive peak off-state cur                                          | rent | I <sub>DRM</sub>    | —       | _    | 2.0                 | mA   | Tj = 150°C, V <sub>DRM</sub> applied                                                                                  |
| On-state voltage                                                       |      | V <sub>TM</sub>     | —       |      | 1.5                 | V    | Tc = $25^{\circ}$ C, I <sub>TM</sub> = 15 A,<br>Instantaneous measurement                                             |
| Gate trigger voltage <sup>Note2</sup>                                  | Ι    | $V_{\text{FGTI}}$   | —       | _    | 1.5                 | V    | $\label{eq:Tj} \begin{array}{l} Tj=25^{\circ}C, \ V_{D}=6 \ V, \ R_{L}=6 \ \Omega, \\ R_{G}=330 \ \Omega \end{array}$ |
|                                                                        | II   | $V_{RGTI}$          | —       | _    | 1.5                 | V    |                                                                                                                       |
|                                                                        | III  | V <sub>RGTIII</sub> | —       | _    | 1.5                 | V    |                                                                                                                       |
| Gate trigger currentNote2                                              | Ι    | IFGTI               | _       |      | 30 <sup>Note6</sup> | mA   | $Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$<br>$R_G = 330 \Omega$                                                  |
|                                                                        | II   | Irgti               | —       | _    | 30 <sup>Note6</sup> | mA   |                                                                                                                       |
|                                                                        | III  | Irgtiii             | —       | _    | 30 <sup>Note6</sup> | mA   |                                                                                                                       |
| Gate non-trigger voltage                                               |      | $V_{GD}$            | 0.2/0.1 |      | —                   | V    | $Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$                                                                   |
| Thermal resistance                                                     |      | Rth (j-c)           | _       | _    | 1.8                 | °C/W | Junction to case <sup>Note3 Note4</sup>                                                                               |
| Critical-rate of rise of off-stat commutating voltage <sup>Note5</sup> | е    | (dv/dt)c            | 10/1    | —    | —                   | V/µs | Tj = 125°C/150°C                                                                                                      |

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured on the  $T_2$  tab.

4. The contact thermal resistance  $R_{th (c-f)}$  in case of greasing is 1.0°C/W.

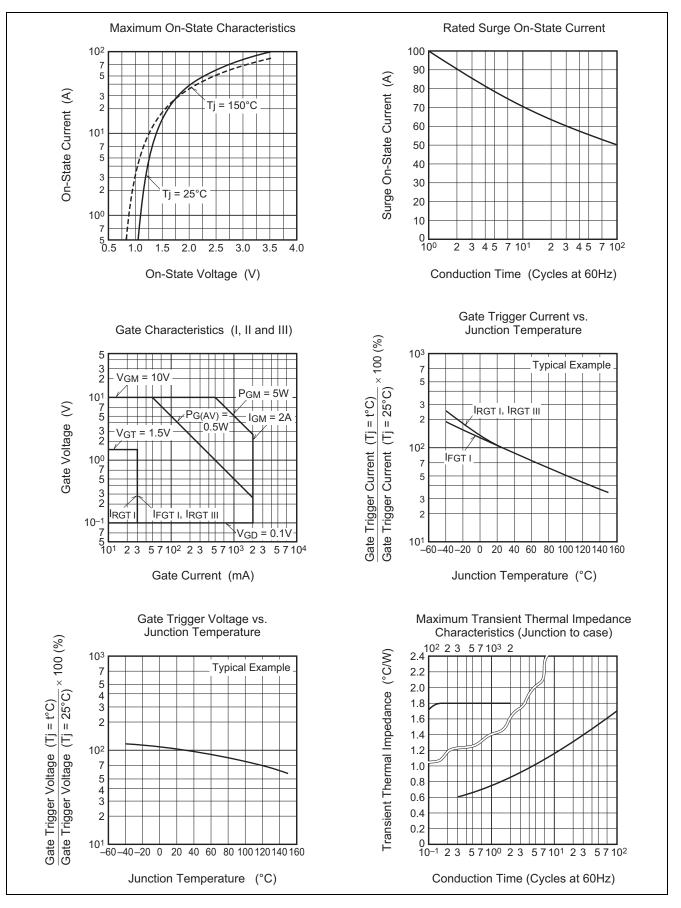
5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

6. High sensitivity (I<sub>GT</sub>  $\leq$  20 mA) is also available. (I<sub>GT</sub> item: 1)

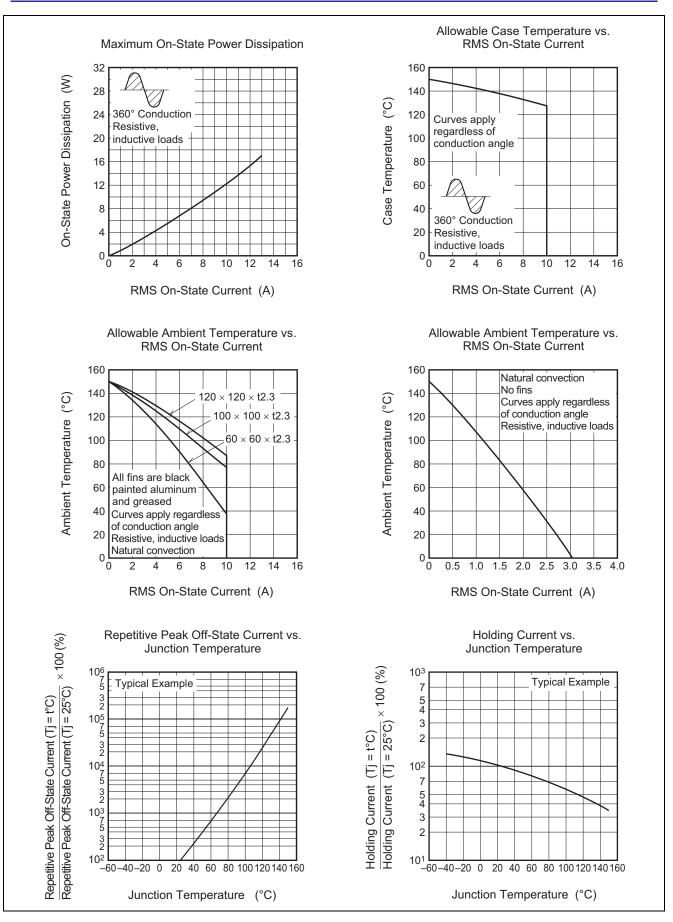
| Test conditions                                                                             | Commutating voltage and current waveforms<br>(inductive load) |
|---------------------------------------------------------------------------------------------|---------------------------------------------------------------|
| 1. Junction temperature<br>Tj = 125°C/150°C                                                 | Supply Voltage → Time                                         |
| <ol> <li>Rate of decay of on-state commutating current<br/>(di/dt)c = - 5.0 A/ms</li> </ol> | Main Current → Time                                           |
| 3. Peak off-state voltage<br>V <sub>D</sub> = 400 V                                         | Main VoltageTime<br>(dv/dt)c V <sub>D</sub>                   |

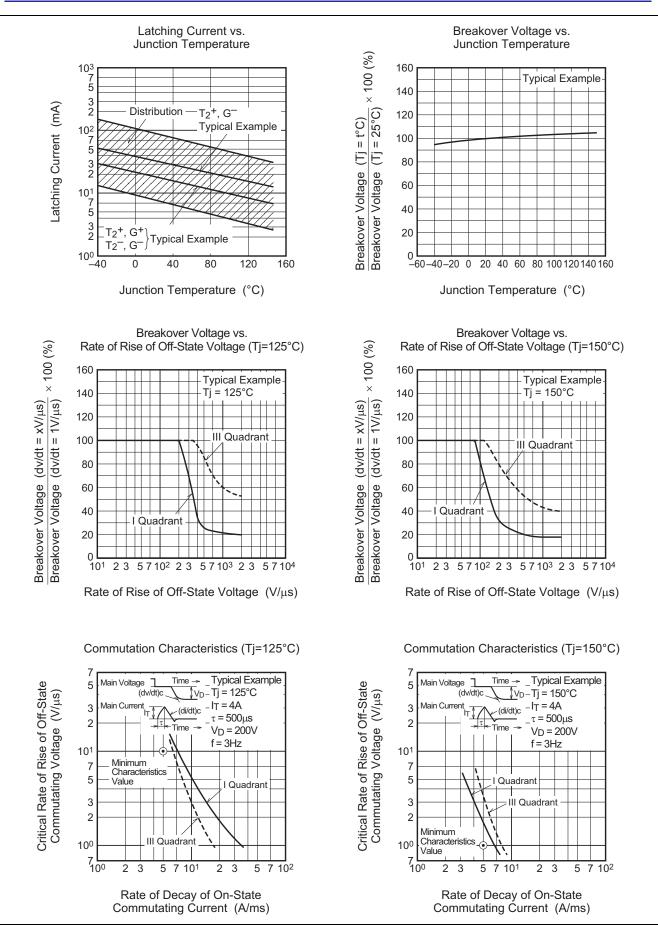


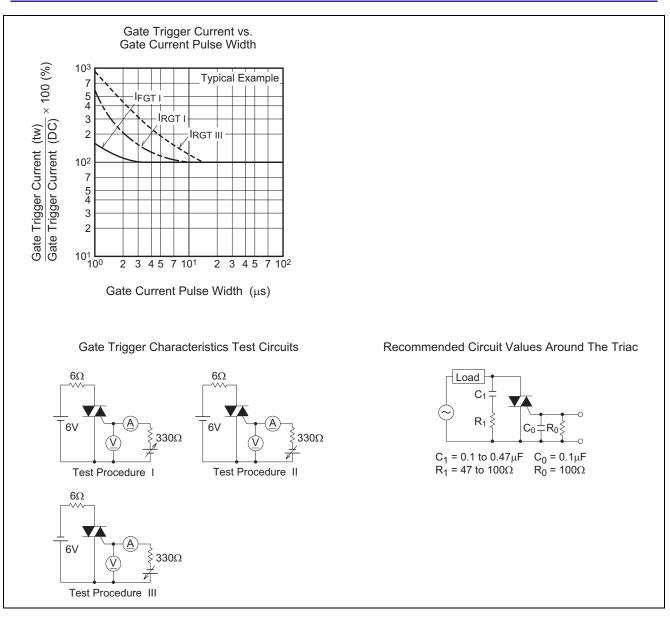
#### **Performance Curves**





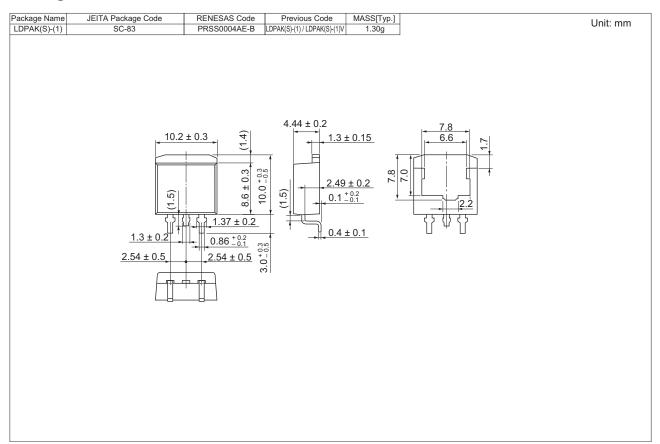


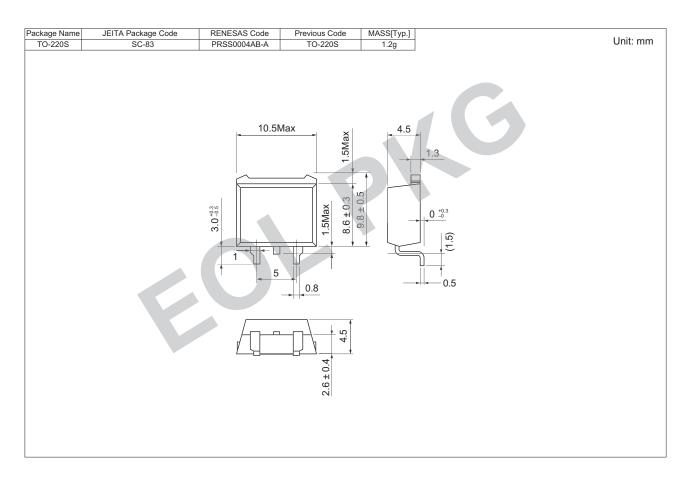






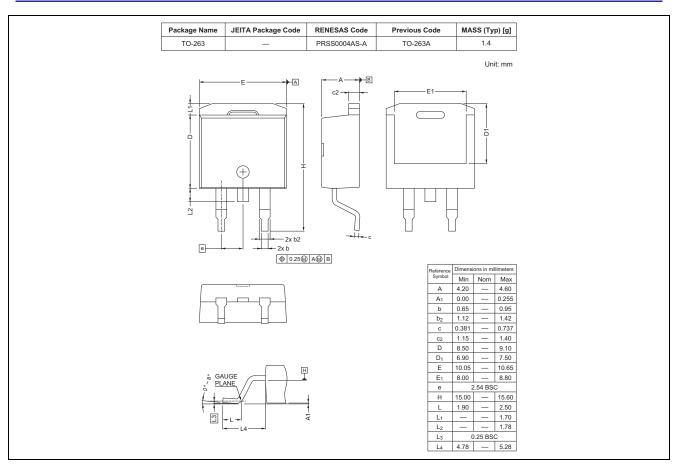
#### **Package Dimensions**

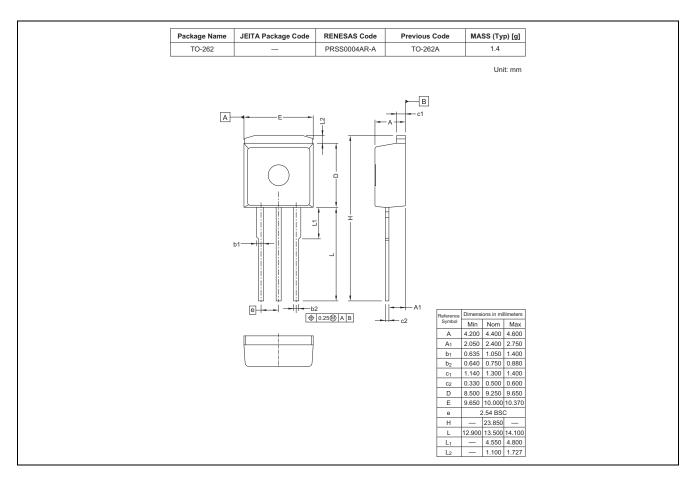






#### BCR10CS-12LB







## **Ordering Information**

| Orderable Part Number | Package      | Packing       | Quantity  | Remark                       |
|-----------------------|--------------|---------------|-----------|------------------------------|
| BCR10CS-12LB#BH0      | TO-263       | Tube          | 50 pcs.   |                              |
| BCR10CS-12LBT1#BH0    | TO-263       | Embossed Tape | 800 pcs.  | Taping direction "T1"        |
| BCR10CS-12LBA1#BH0    | TO-262       | Tube          | 50 pcs.   |                              |
| BCR10CS-12LB#B00      | LDPAK(S)-(1) | Tube          | 50 pcs.   | Not Recommend for New Design |
| BCR10CS12LBT11#B00    | LDPAK(S)-(1) | Embossed Tape | 1000 pcs. | Not Recommend for New Design |
| BCR10CS-12LB#B01      | TO-220S      | Tube          | 50 pcs.   | EOL                          |
| BCR10CS12LBT11#B01    | TO-220S      | Embossed Tape | 1000 pcs. | EOL                          |

Note : Please confirm the specification about the shipping in detail.



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